L Number	Hits	Search Text	DB	Time stamp
•	4	((xide-nitride r xynitride r xy-nitride) near2 gate near2 (insulator or insulating	USPAT; US-PGPUB;	2003/12/11 13:43
		dielectric)).clm. and (oxide near2 gate	EPO; JPO;	10.43
		near2 (dielectric or insulating or	DERWENT;	
		insulator)).clm.	IBM_TDB	
-	2780	((ozone or ozonated or ozonating)) same	USPAT;	2003/12/11
		oxide same film	US-PGPUB;	13:44
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	10573	((ozone or ozonated or ozonating)) same	USPAT;	2003/12/11
		(oxide)	US-PGPUB;	13:44
			EPO; JPO;	13144
			DERWENT;	ĺ
			IBM_TDB	
	42	(oxide adj film).clm. and (ozone or	USPAT;	2003/12/11
		ozonating or ozonated or ozonation).clm.	US-PGPUB;	13:45
		and (silicon adj nitride adj film).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
ļ	9	(oxide adj film).clm. same (ozone or	USPAT;	2003/12/11
		ozonating or ozonated or ozonation).clm.	US-PGPUB;	13:45
		same(silicon adj nitride adj film).clm.	EPO; JPO;	101-10
		, , , , , , , , , , , , , , , , , , , ,	DERWENT;	
	į		IBM_TDB	
-	9	(oxide adj film).clm. same (ozone or	USPAT;	2003/12/11
		ozonating or ozonated or ozonation).clm.	US-PGPUB;	13:46
		same (silicon adj nitride adj film).clm.	EPO; JPO;	
	İ	• • •	DERWENT;	
			IBM_TDB	
-	0	(oxide adj (layer or film)).clm. same	USPAT;	2003/12/11
		(ozonating or ozonated or ozonation).clm.	US-PGPUB;	13:47
		same (silicon adj nitride adj (layer or	EPO; JPO;	- -
		film)).clm.	DERWENT;	
			IBM_TDB	
-	0	(oxide adj (layer or film)).clm. same	USPAT;	2003/12/11
		(ozonating or ozonated or ozonation).clm.	US-PGPUB;	13:48
		same (((silicon adj nitride) or SiN) adj (layer	EPO; JPO;	
		or film)).clm.	DERWENT;	
			IBM_TDB	
-	0	(oxide adj (layer or film)).clm. and	USPAT;	2003/12/11
		(ozonating or ozonated or ozonation).clm.	US-PGPUB;	13:48
		and (((silicon adj nitride) or SiN) adj (layer	EPO; JPO;	-
į		r film)).clm.	DERWENT;	
		••	IBM_TDB	
	0	(oxide adj (layer or film)) and (zonating or	USPAT;	2003/12/11
		zonated or zonati n).clm. and (((silicon	US-PGPUB;	13:48
		adj nitride) r SiN) adj (lay r or film))	EPO; JPO;	
		- , , , , , , , , , , , , , , , , , , ,	DERWENT;	
			IBM_TDB	

-	354	(oz nated or zonating or ozonation r	USPAT;	2003/12/11
		ozonate).clm.	US-PGPUB;	13:49
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6	((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate) near (substrate or substance or	US-PGPUB;	13:49
		element)).clm.	EPO; JPO;	ļ
			DERWENT;	
			IBM_TDB	ļ
-	114	((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate)) near10 (film or layer)	US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	17	(((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate)) near10 (film or layer)).clm.	US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	(((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate)) near10 (film)).clm.	US-PGPUB;	13:50
			EPO; JPO;	
	İ		DERWENT;	
			IBM_TDB	
-	5	(((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate)) near10 (film or layer) near10	US-PGPUB;	13:52
		oxide).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate)) near10 (film or layer) near10	US-PGPUB;	13:52
		oxide).clm. and nitride	EPO; JPO;	
			DERWENT;	
			IBM TDB	